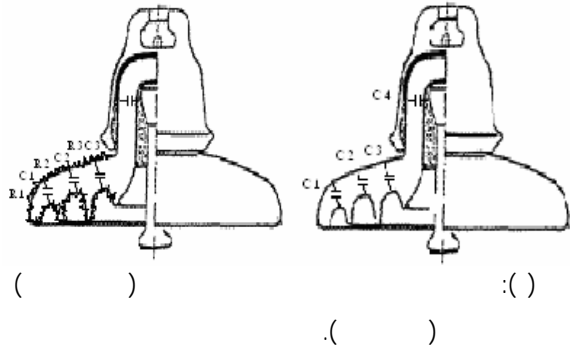


¹ amin_lafzi@yahoo.com, ² farhadshahnia@yahoo.com, ³ ahrabian@tabrizu.ac.ir

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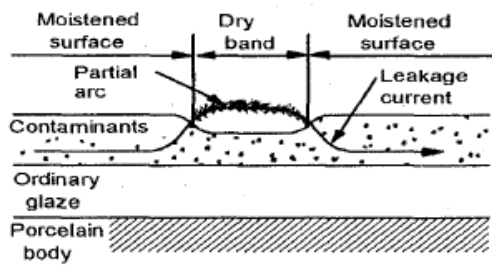
Tin-Oxide (SnO_2)

niobium-oxide (Nb_2O_5) antimony (Sb^{+5})

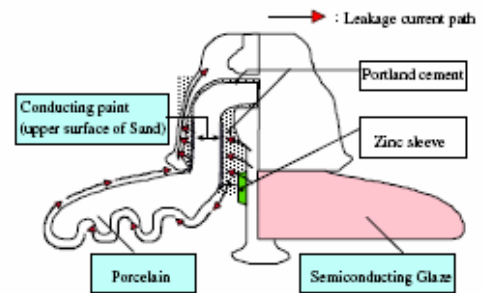
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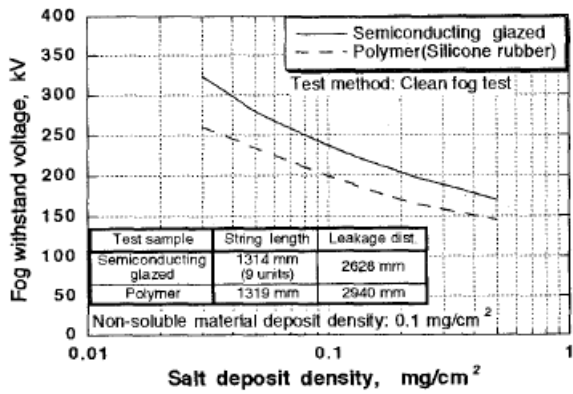
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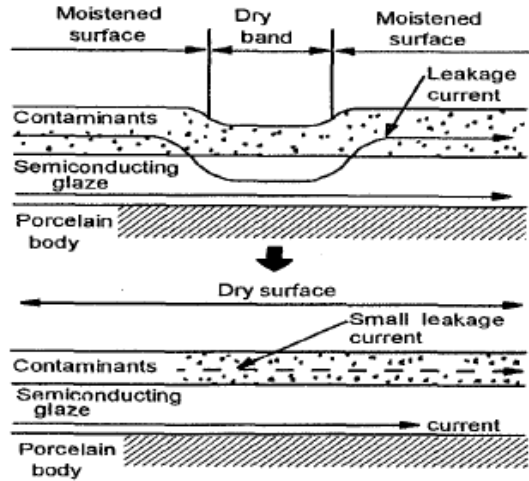
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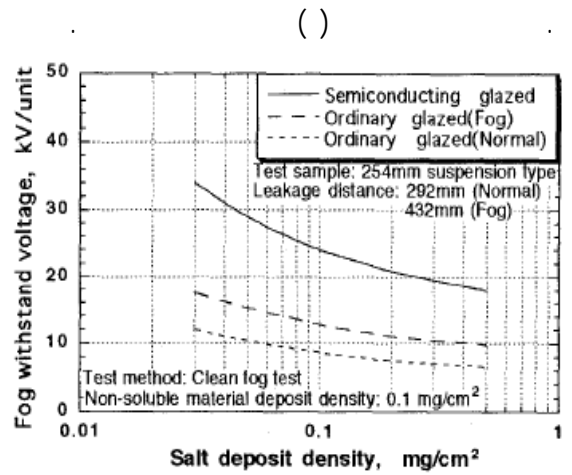
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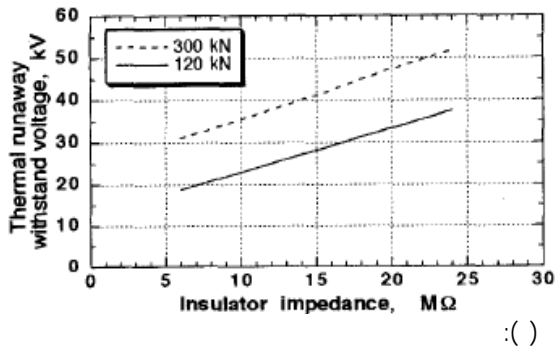
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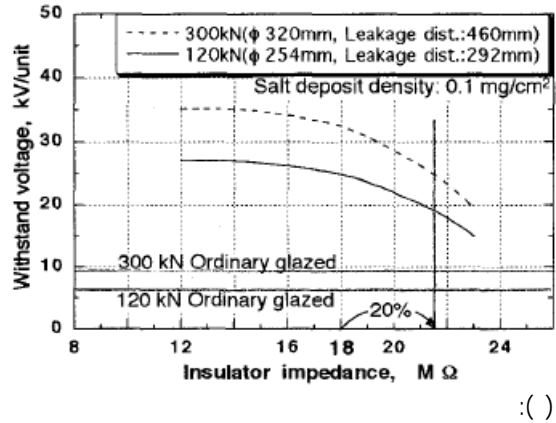
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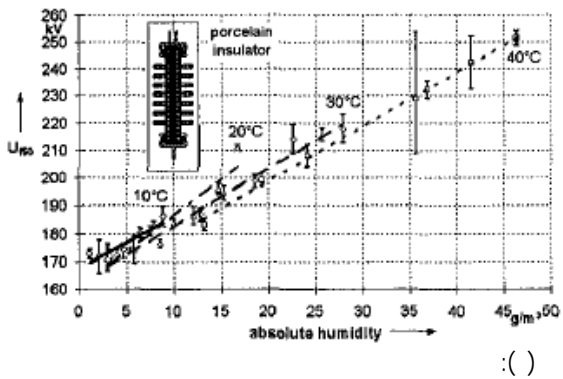


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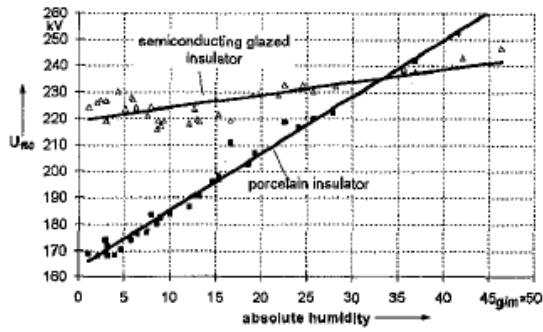
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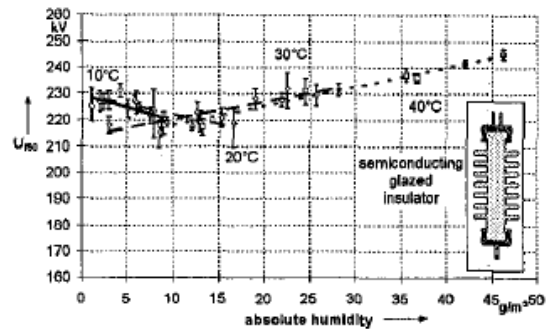
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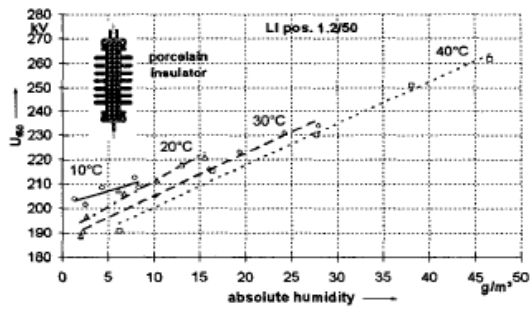
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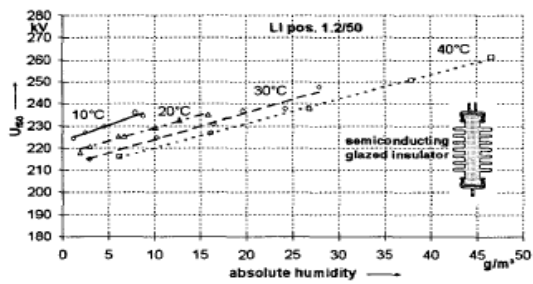
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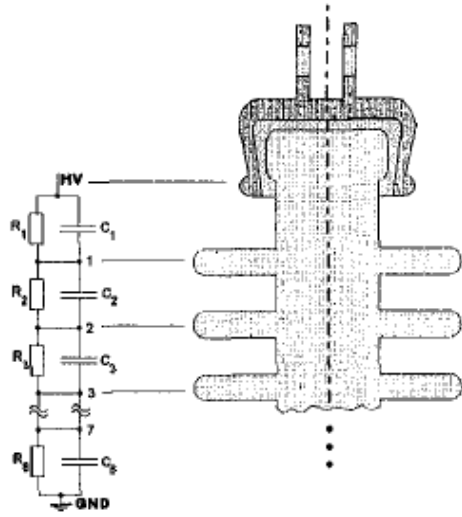


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$$\left(\frac{g}{m^3} \right)$$

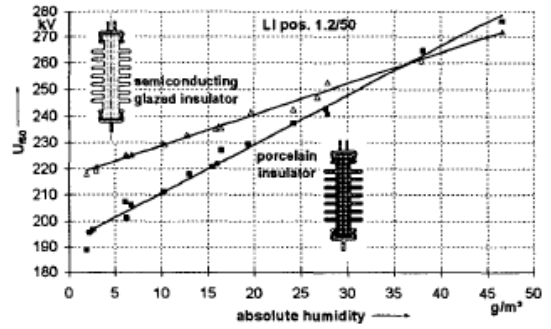
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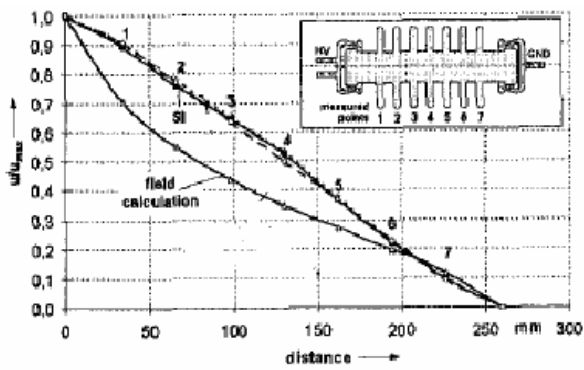
$$\frac{g}{m^3}$$



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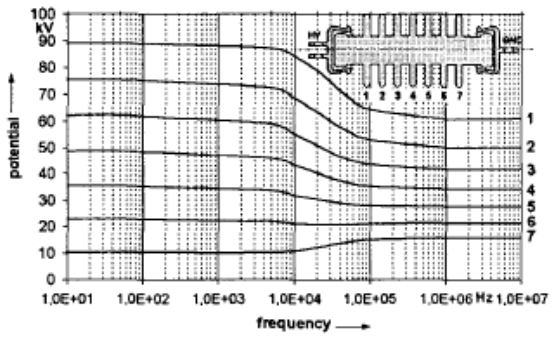


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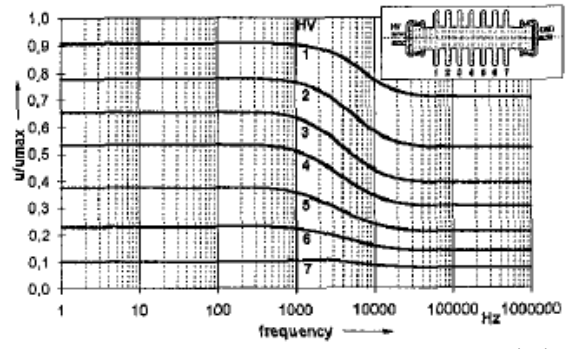
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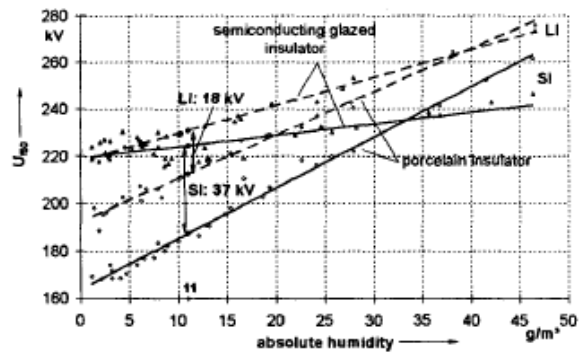


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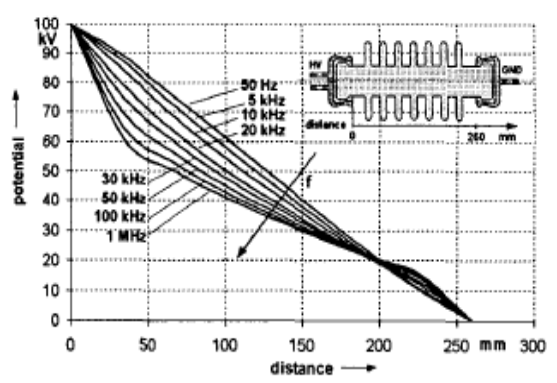
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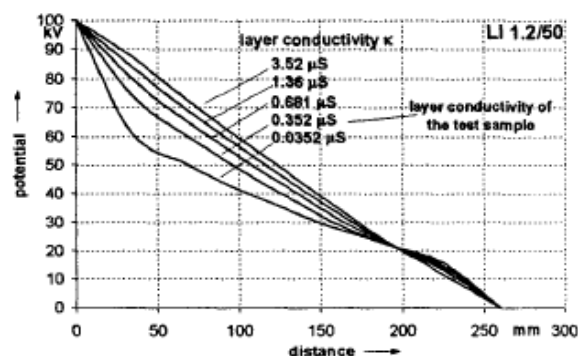


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